

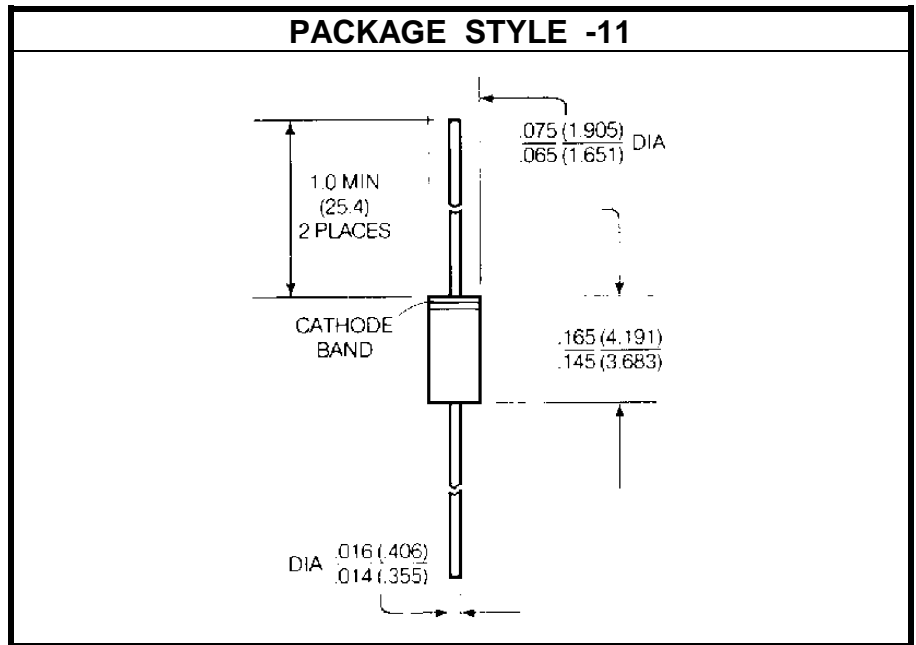
SILICON PIN DIODE

DESCRIPTION:

The **AP1266** is a Passivated Epitaxial Silicon PIN Diode in a Hermetically Sealed Glass Package Designed for Large Signal Switches.

MAXIMUM RATINGS

I	100 mA
V	200 V
P_{DISS}	1.0 W @ T _C = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +175 °C
T_{SOLD}	200 °C



CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I _R = 10 μA	200			V
C_T	V = 50 V f = 1.0 MHz			1.5	pF
R_S	I _F = 50 mA f = 100 MHz			0.6	Ohms
T_L	I _F = 10 mA I _R = 6.0 mA		3.0		μS
I-REGION	I-REGION WIDTH		3.0		mS